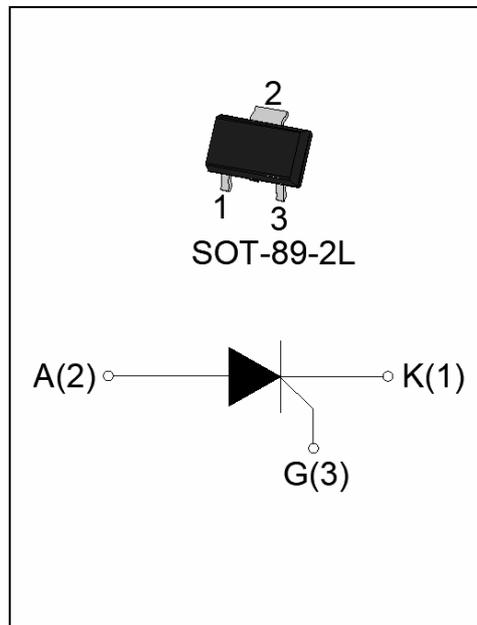




The JX020N2 SCR provides high dV/dt rate with strong resistance to electromagnetic interface. It is especially recommended for use on residual current circuit breaker, straight hair, igniter etc. Package SOT-89-2L is RoHS compliant.

Symbol	Value	Unit
$I_{T(RMS)}$	2	A
V_{DRM} / V_{RRM}	600	V
I_{GT}	200	μA



Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-125	
Repetitive peak off-state voltage ($T_j=25^\circ C$)	V_{DRM}	600	V
Repetitive peak reverse voltage ($T_j=25^\circ C$)	V_{RRM}	600	V
Average on-state current ($T_c = 59^\circ C$)	$I_{T(AV)}$	1.3	A
RMS on-state current ($T_c = 59^\circ C$)	$I_{T(RMS)}$	2	A
Non repetitive surge peak on-state current ($t_p=10ms, T_j=25^\circ C$)	I_{TSM}	20	A
Non repetitive surge peak on-state current ($t_p=8.3ms, T_j=25^\circ C$)		22	
I^2t value for fusing ($t_p=10ms, T_j=25^\circ C$)	I^2t	2	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}, f=100Hz, T_j=125^\circ C$)	di/dt	50	$A/\mu s$
Peak gate current ($t_p=20\mu s, T_j=125^\circ C$)	I_{GM}	1.2	A
Average gate power dissipation ($T_j=125^\circ C$)	$P_{G(AV)}$	0.2	W

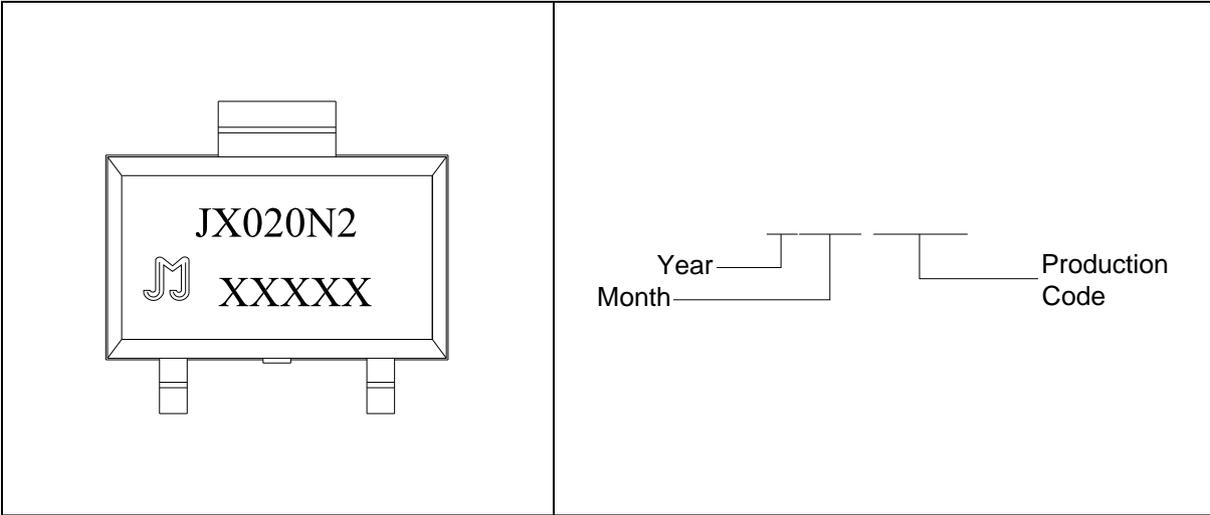
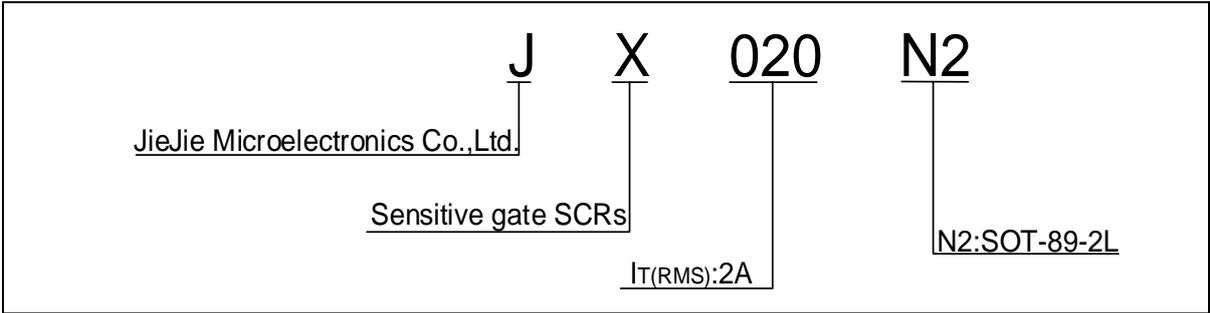




FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

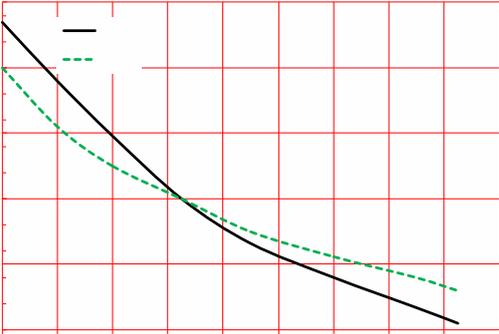
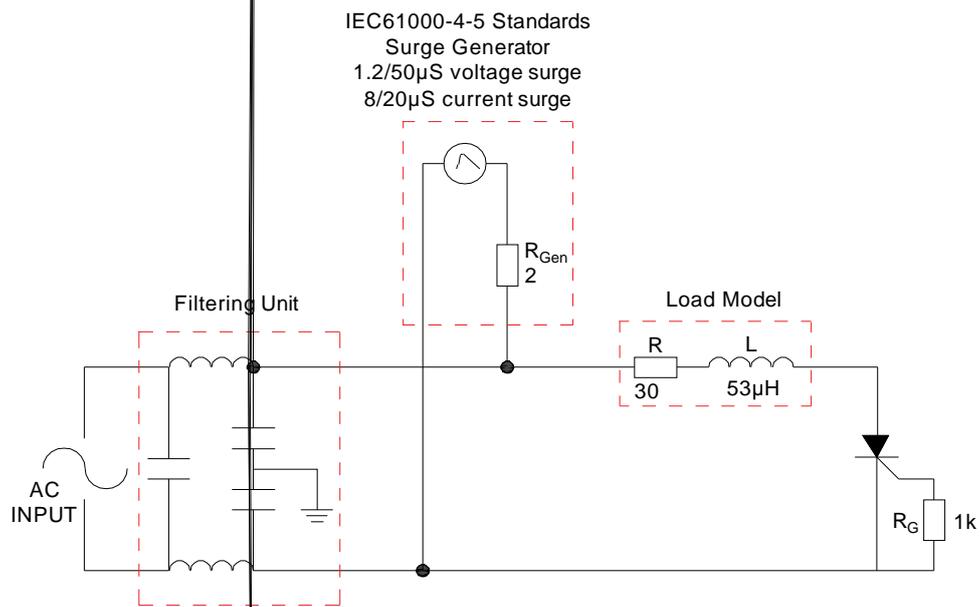


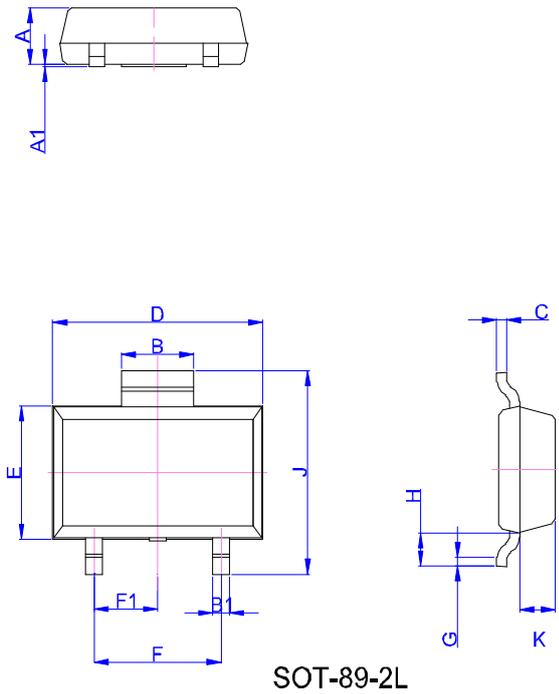
FIG.8 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



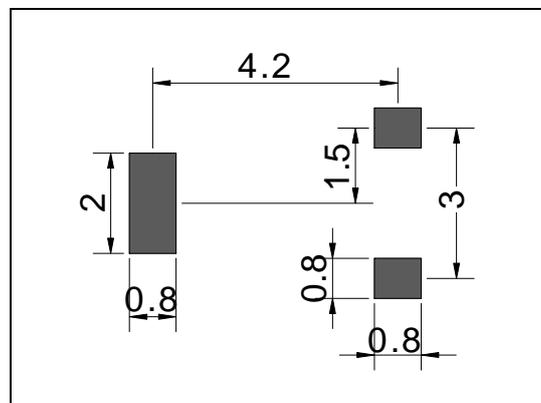
Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(μ A)	Package	Base qty. (pcs)	Delivery mode
JX020N2	600	200	SOT-89-2L	4,000	Tape & Reel

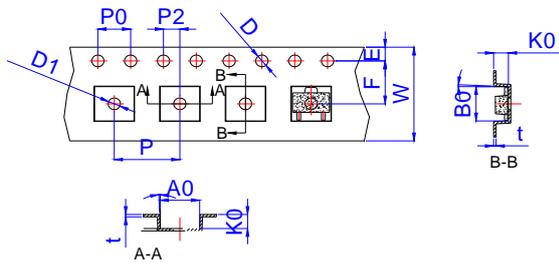
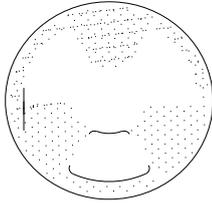
Document Revision History

Date	Revision	Changes
Apr.12, 2023	A.1.0	Last update



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	1.3	1.4	1.5	0.051	0.055	0.059
A1	0.01	0.06	0.10	0.001	0.002	0.004
B	1.6	1.7	1.8	0.063	0.067	0.071
B1	0.3	0.4	0.5	0.012	0.016	0.020
C	0.22	0.254	0.32	0.009	0.010	0.013
D	4.75	4.95	5.15	0.187	0.195	0.203
E	2.90		3.30	0.114		0.130
F	2.80		3.20	0.110		0.126
F1	1.40		1.60	0.055		0.063
G	0.20	0.30	0.40	0.008	0.012	0.016
H	0.58	0.78	0.98	0.023	0.031	0.039
J	4.30	4.50	4.70	0.169	0.177	0.185
K	0.80		1.00	0.031		0.039





Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
E	1.65	1.75	1.85	0.065	0.069	0.073
F	5.45	5.50	5.55	0.215	0.217	0.219
P2	1.90	2.00	2.10	0.075	0.079	0.082
D	-	1.50	1.60	-	0.059	0.063
D1	1.50	-	-	0.059	-	-
P0	3.90	4.00	4.10	0.154	0.157	0.161
10P0	39.80	40.00	40.20	1.567	1.575	1.583
W	-	-	12.30	-	-	0.482
P	7.90	8.00	8.10	0.311	0.315	0.319
A0	5.20	5.30	5.40	0.204	0.208	0.212
B0	4.80	4.90	5.00	0.188	0.192	0.196
K0	1.75	1.85	1.95	0.069	0.073	0.076
t	0.20	0.25	0.30	0.008	0.010	0.012
	3°		5°	3°		5°

Information furnished in this document is believed to be accurate and reliable. However, Jiangsu JieJie Microelectronics Co., Ltd. assumes no responsibility for the consequences of use without consideration for such information nor use beyond it. Information mentioned in this document is subject to change without notice, apart from that when an agreement is signed, Jiangsu JieJie complies with the agreement. Products and information provided in this document have no infringement of patents. Jiangsu JieJie assumes no responsibility for any infringement of other rights of third parties which may result from the use of such products and information. This document supersedes and replaces all information previously supplied.

 is a registered trademark of Jiangsu JieJie Microelectronics Co., Ltd.
Copyright ©2023 Jiangsu JieJie Microelectronics Co., Ltd. Printed All rights reserved.